



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

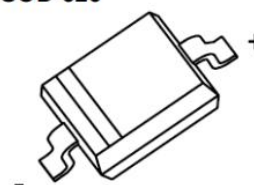
B5817WS-B5819WS

SOD-323 Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

■ Features 特点

Low forward voltage drop 低正向压降
 High current capability 高电流能力
 Surface mount device 表面贴装器件
 Case 封装:SOD-323

SOD-323



■ Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

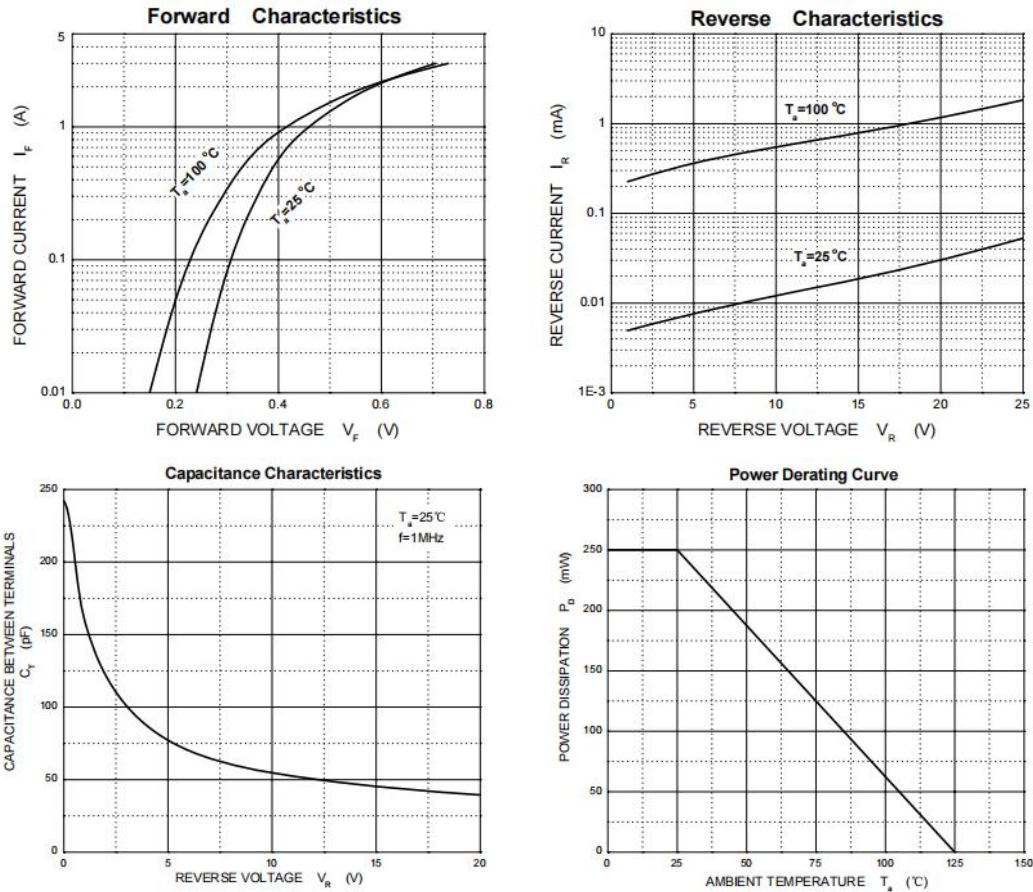
Characteristic 特性参数	Symbol 符号	B5817WS	B5818WS	B5819WS	Unit 单位
Device Marking 产品印字		SJ	SK	SL	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	20	30	40	V
DC Reverse Voltage 直流反向电压	V_R	20	30	40	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	14	21	28	V
Forwards Rectified Current 正向整流电流	I_F	1			A
Peak Surge Current 峰值浪涌电流	I_{FSM}	9			A
Repetitive Peak Surge Current 重复峰值浪涌电流	I_{FRM}	1.5			A
PoWer Dissipation 耗散功率	P_D	250			mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	500			$^{\circ}\text{C}/\text{W}$
Junction/Storage Temperature 结温/储藏温度	T_J, T_{stg}	-50to+150 $^{\circ}\text{C}$			$^{\circ}\text{C}$

■ Electrical Characteristics 电特性

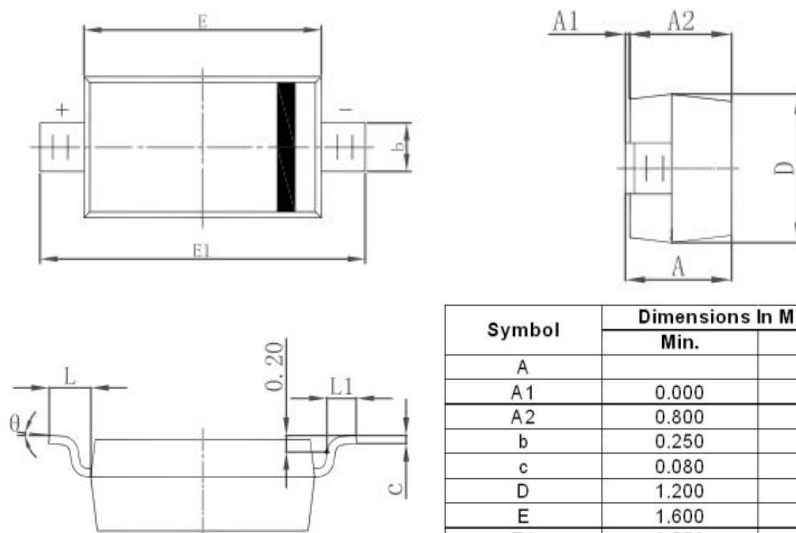
($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	B5817WS	B5818WS	B5819WS	Unit 单位	Condition 条件
Reverse Voltage 反向电压	V_R	20	30	40	V	$I_R=1\text{mA}$
Forwards Voltage 正向电压	V_F	0.45 0.75	0.55 0.875	0.6 0.9	V	$I_F=1\text{A}$ $I_F=3\text{A}$
Reverse Current 反向电流	I_R	1			mA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_T	120			pF	$V_R=4\text{V}, f=1\text{MHz}$

Typical Characteristic Curve 典型特性曲线



Dimension 外形封装尺寸 SOD-323



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A		1.000		0.039
A1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.475 REF.		0.019 REF.	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°